SuperMOS – SOT-323 60V BV_{DSS}, 1.5Ω $R_{DS(on)}$, N-channel MOSFET

1. Description

The BSS138BKW is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product BSS138BKW is Pb-free.

2. Features

- 60V, $R_{DS(ON)}$=1.5Ω(TYP.) @V_{GS}=10V
  $R_{DS(ON)}$=1.6Ω(TYP.) @V_{GS}=4.5V
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
BSS138BKW	SOT-323	38KQ	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

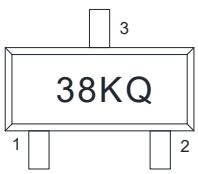
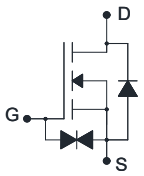
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

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6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 ˚C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	0.36	A
Maximum Power Dissipation	P_D	236	mW
Pulsed Drain Current [a]	I_{DM}	1.44	A
Operating Junction Temperature	T_J	150	°C
Lead Temperature	T_L	260	°C
Storage Temperature Range	T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation			
Parameter	Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	530	°C/W

Note:

a: Repetitive rating, pulse width limited by junction temperature, tp=10μs, Duty Cycle=1%

Electrical Characteristics

At TA = 25℃ unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=10mA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V,TJ=25℃			1.0	uA
		V_{DS}=40V, V_{GS}=0V, TJ=125℃			100	
Gate-to-source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	uA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=250uA	0.8	1.0	1.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=0.3A		1.5	1.9	Ω
		V_{GS}=4.5V, I_D=0.2A		1.6	2.5	
		V_{GS}=2.5V, I_D=0.1A		2.7	4.5	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS}=0V, f=1MHz, V_{DS} =25V		25	50	pF
Output Capacitance	C_{OSS}			9.7	22	
Reverse Transfer Capacitance	C_{RSS}			2.2	5	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS}=4.5V, V_{DS}=25V, I_D=0.3A		0.65	1	nC
Gate-to-Source Charge	Q_{GS}			0.2		
Gate-to-Drain Charge	Q_{GD}			0.23		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	V_{GS}=10V, V_{DS}=25V, I_D=0.3A, R_G=6Ω		2.3	5	ns
Rise Time	t_r			19.2	40	
Turn-Off Delay Time	$t_{d(OFF)}$			6.3	12	
Fall Time	t_f			23	50	
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS}=0V, I_S=0.5A		0.86	1.5	V

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7. Typical Characteristic

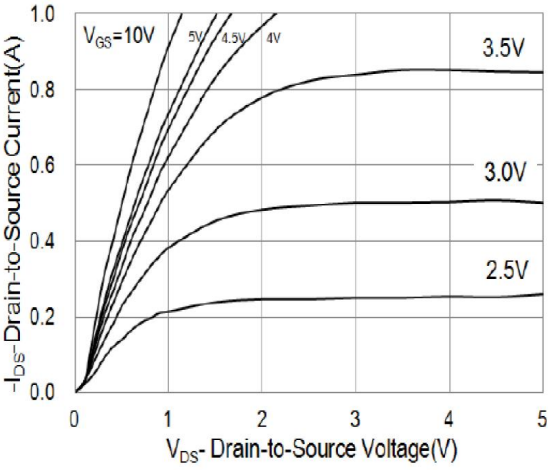


Fig.1 On-Region Characteristics

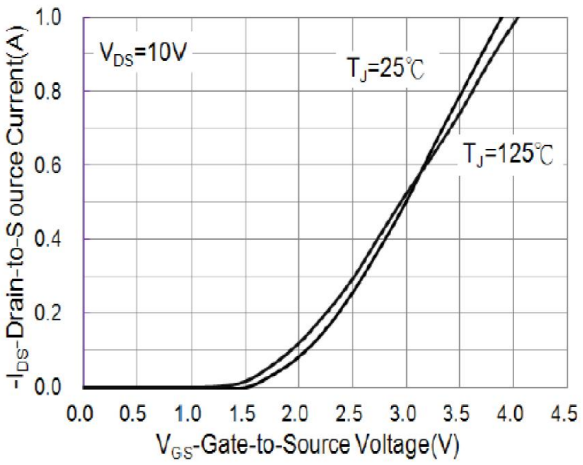


Fig.2 Transfer Characteristics

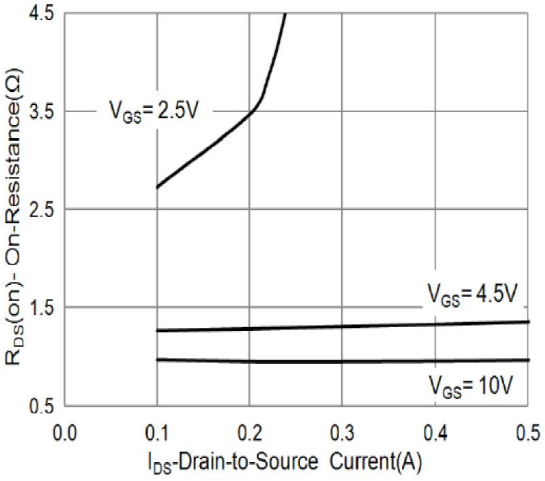


Fig.3 On-Resistance vs. Drain Current

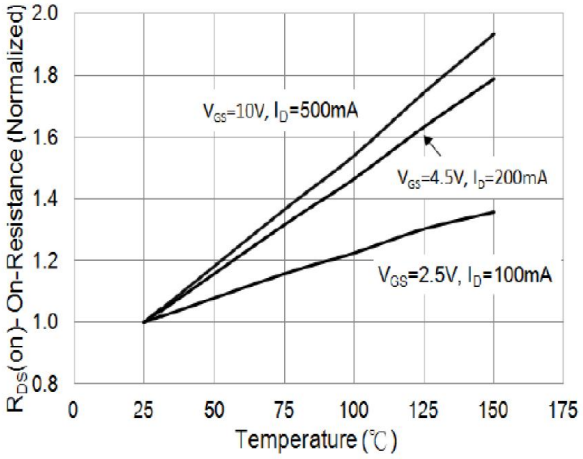


Fig.4 On-Resistance vs. Junction temperature

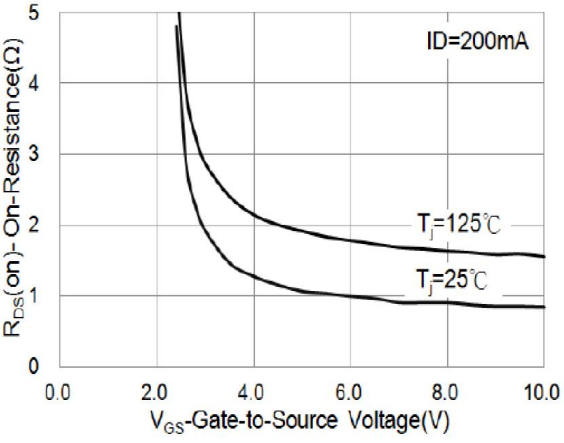


Fig.5 On-Resistance Variation with VGS

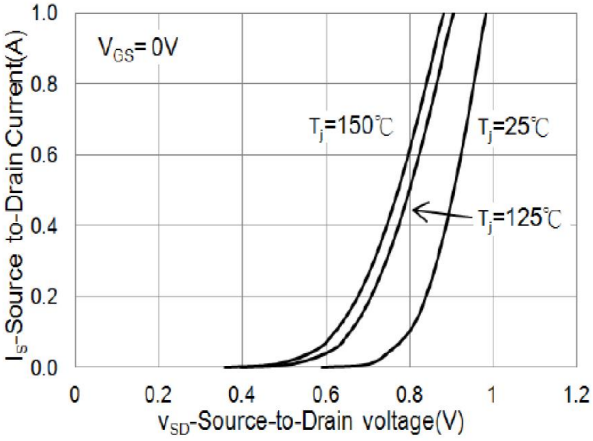


Fig.6 Body Diode CharacterIsIcs

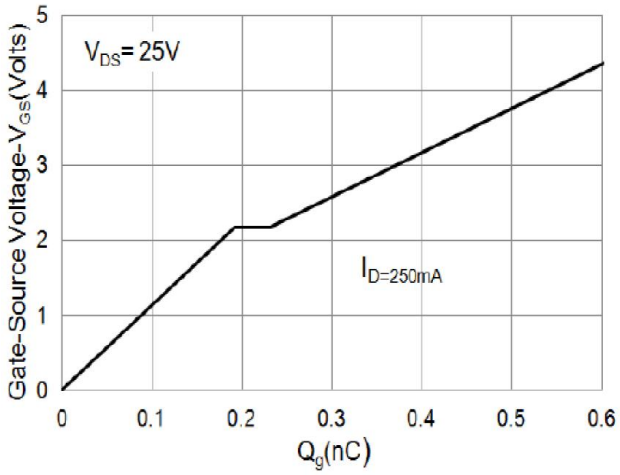


Fig.7 Gate-Charge Characteristics

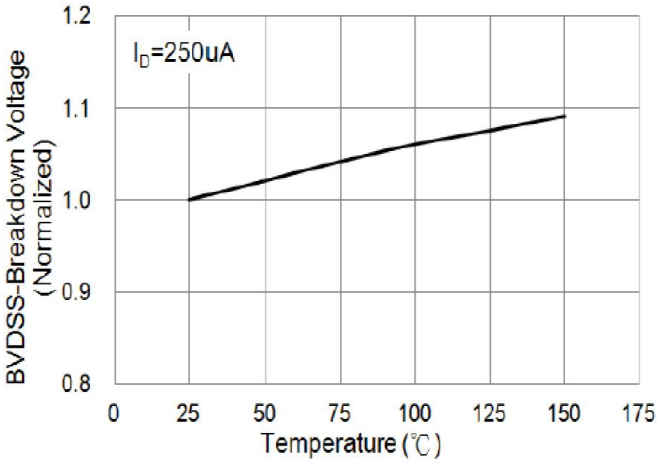


Fig.8 Breakdown Voltage Variation vs. Temperature

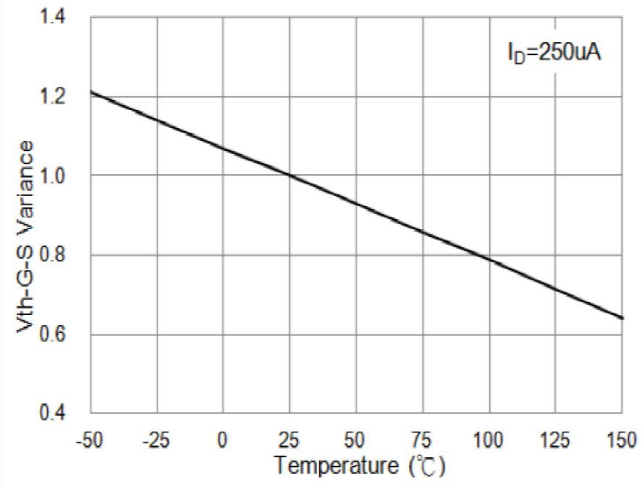


Fig.9 Threshold Voltage Variation with Temperature

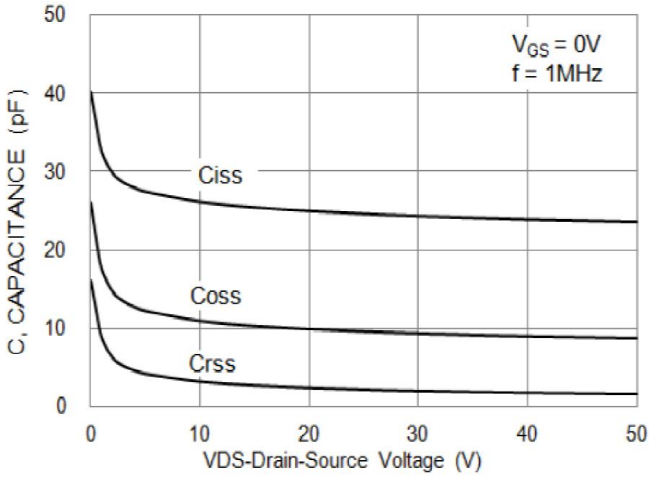
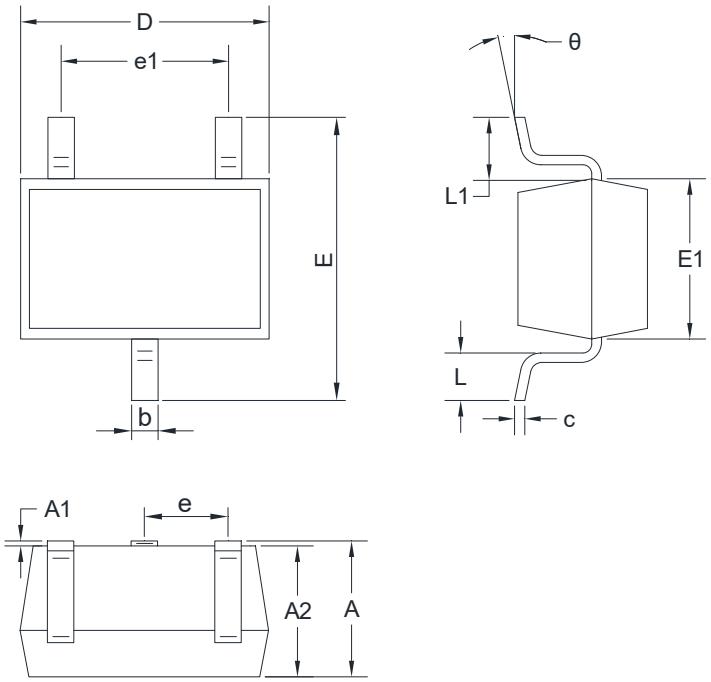


Fig.10 Capacitance vs. Drain-Source Voltage.

8. Dimension and Patterns (SOT-323)



Symbol	Millimeters		Symbol	Millimeters	
	Min	Max		Min	Max
A	0.90	1.10	E1	1.15	1.35
A1	0.00	0.10	e	0.65 TYP	
A2	0.90	1.00	e1	1.20	1.40
b	0.20	0.40	L	0.26	0.46
c	0.08	0.15	L1	0.525 REF	
D	2.00	2.20	θ	0°	8°
E	2.15	2.45			

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